

## Features

- Frequency: 0.01~50GHz
- Gain: 8dB
- NF: 7dB@30GHz
- Output P<sub>1dB</sub>: 13dBm@40GHz
- Supply Voltage: +8V@130mA
- Die Size: 3.54mmx1mmx0.1mm

## Typical Applications

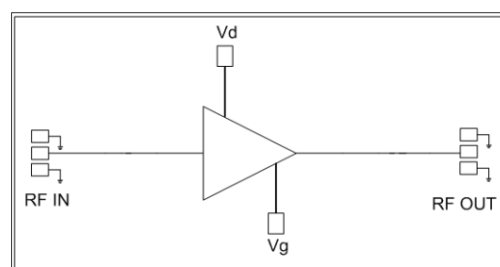
- RF/ Microwave radio
- Military and Space
- Test and Measurement
- Fiber Optics

## General Description

SAC3940 is a GaAs MMIC traveling wave structured amplifier die which operates between 100MHz to 50GHz. The amplifier can provide 8dB gain, 13dBm Output P<sub>1dB</sub> from a 130mA supply current at +8V.

The chip offers full passivation for increased reliability and moisture protection.

## Functional Diagram



## Electrical Performance (T<sub>A</sub>=25°C, V<sub>d</sub>=+8V, I<sub>D</sub>=130mA, Z<sub>0</sub>=50Ω)

| Parameter                        | Min.    | Typ. | Max. | Units |
|----------------------------------|---------|------|------|-------|
| Frequency Range                  | 0.01~50 |      |      | GHz   |
| Gain                             | —       | 8    | —    | dB    |
| Gain Flatness                    | —       | ±1.5 | ±2   | dB    |
| Reverse Isolation                | —       | -40  | -15  | dB    |
| Input VSWR                       | -8      | -12  | —    | dB    |
| Output VSWR                      | -8      | -12  | —    | dB    |
| Noise Figure                     | —       | 7    | 10   | dB    |
| Output P <sub>1dB</sub>          | 11      | 13   | —    | dBm   |
| Supply Current (I <sub>D</sub> ) | —       | 130  | 180  | mA    |

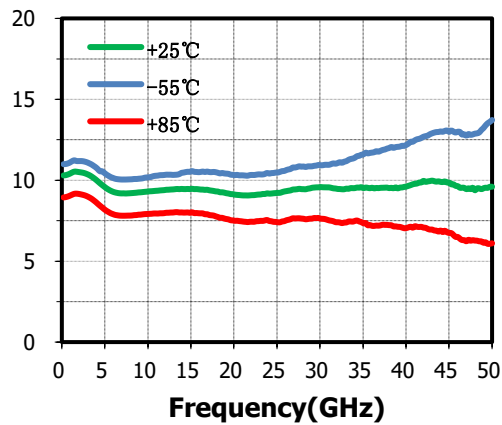
## Absolute Maximum Ratings

|                     |        |                       |              |
|---------------------|--------|-----------------------|--------------|
| Maximum Input Power | +12dBm | Operating Temperature | -55°C~+85°C  |
| Channel Temperature | +150°C | Storage Temperature   | -65°C~+150°C |
| Working Voltage     | +10V   |                       |              |

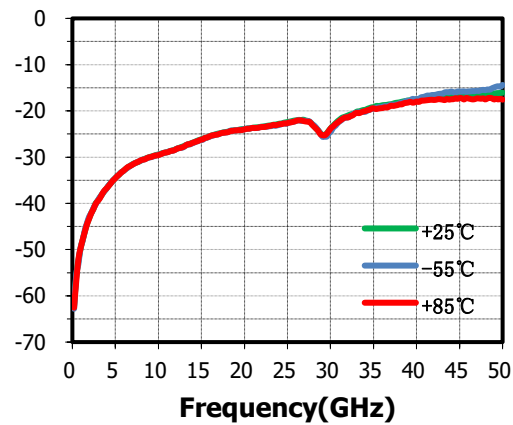
## Typical Performance Curve

VD=+8V, I<sub>DQ</sub>=130mA, On probe

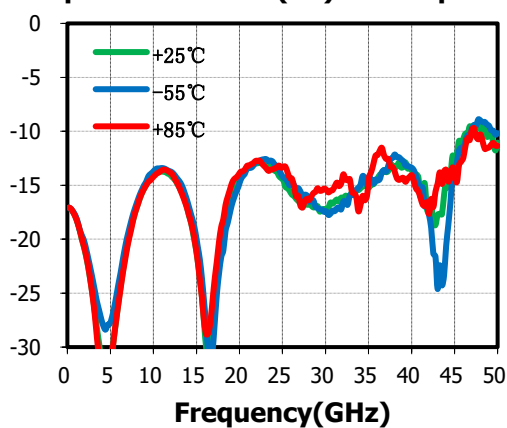
**Small Signal Gain(dB) vs.Temperature**



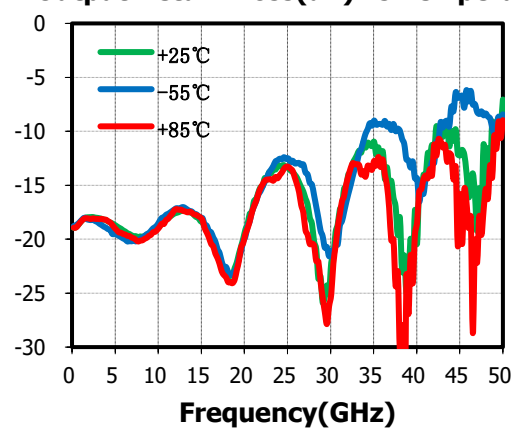
**Isolation(dB) vs.Temperature**



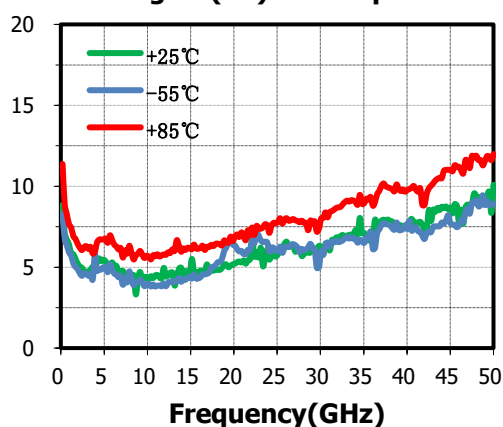
**Input Return Loss(dB) vs.Temperature**



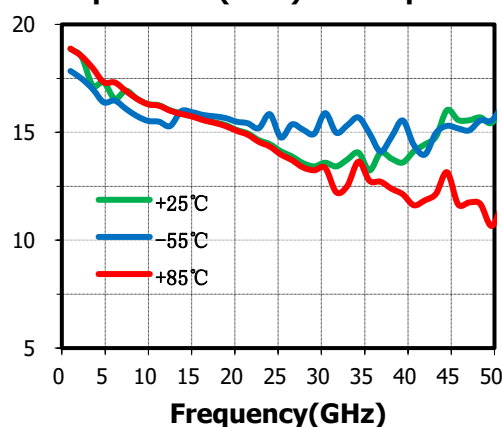
**Output Return Loss(dB) vs.Temperature**



**Noise Figure(dB) vs.Temperature**



**Output P-1dB(dBm) vs.Temperature**





Rev 1.0

## Assembly Diagram



1. The GaAs MMIC device is susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.
2. The MMIC should be stored in dry Nitrogen gas environment and be handled in clean room.
3. RF connections should be made as short as possible to reduce the inductive effect of the bond wire. The distance between RF pads and the substrate is no more than 50um. Please use diameter of 25um double Au wires with its length between 150 to 200um.
4. The backside of SAC3940 is RF grounded. Die attach should be accomplished with electrically and thermally conductive epoxy or Au/Sn soldering with its temperature not surpassing 300 degrees centigrade and the time of period being smaller than 30 seconds.